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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	NEW- 10/736617	
			Filing Date	December 12, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	N/A 2824B	
			Examiner Name	Not Yet Assigned V. Yeusikov	
Sheet	1	of	8	Attorney Docket Number	M4065.0698/P698-A

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
AA	6,473,332		10/2002	Ignatiev et al.		
AB	4,316,946		1/1982	Masters, et al.		
AC	4,419,421		12/1983	Wichelhaus, et al.		
AD	6,487,106		11/26/2002	Kozicki		
AE	5,314,772		5/24/1994	Kozicki		
AF	2002/0190350 APP		12/19/2002	Kozicki		
AG	2003/0027416 APP		2/6/2003	Moore		
AH	2003/0001229 APP		1/2/2003	Moore et al.		
AI	2002/0127886 APP		9/12/2002	Moore et al.		
AJ	2002/0123170 APP		9/5/2002	Moore et al.		
AK	2002/0163828 APP		11/2002	Krieger et al.		
AL	6,072,716		6/2000	Jacobson et al.		
AM	5,272,359		12/93	Nagasubramanian et al.		
AN	4,671,618		6/87	Wu et al.		
AO	4,800,526		1/89	Lewis		
AP	2003/0035314		02/20/03	Kozicki		
AQ	2003/0035315		02/20/03	Kozicki		
AR	US 2002/0168820		11/14/2002	Kozicki et al.		
AS	6,469,364		10/22/2002	Kozicki		
AT	6,368,324		05/14/2002	Kozicki et al.		
AU	US 2002/0000666		01/03/2002	Kozicki et al.		
AV	5,500,532		03/19/1996	Kozicki et al.		

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Country Code ³	Number ⁴ -Kind Code ⁵ (if known)				
VY	BA	WO	97/48032	12/18/1997	Kozicki et al.		
VY	BB	WO	95/28914	06/10/1999	Kozicki et al.		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 601.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
VY	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃ Te ₅ chalcogenide glass, Vacuum 59 (2000) 845-853.	
VY	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
VY	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous	

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		Filing Date	December 12, 2003
		First Named Inventor	Kristy A. Campbell
		Art Unit	N/A 2829
		Examiner Name	Not Yet Assigned Yevsi Kov
		Attorney Docket Number	M4065.0698/P698-A
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		alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
✓	CD	Affifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system $\text{Se}_{75}\text{Ge}_{25-x}\text{Sbx}$, Appl. Phys. A 55 (1992) 167-169.	
✓	CE	Affifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe_{1-x} , Egypt, J. Phys. 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag_2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
	CM	Belin, R.; Tallades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag_7GeSe_5 : non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.	
	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M- Ag_2Se -M, Thin solid films 70 (1980) L1-L4.	
	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CR	Bernede, J.C., Switching and silver movements in Ag_2Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
	CT	Bernede, J.C.; Conan, A.; Fousenat, E.; El Bouchalri, B.; Goureaux, G., Polarized memory switching effects in $\text{Ag}_2\text{Se}/\text{Se}/\text{M}$ thin film sandwiches, Thin solid films 97 (1982) 165-171.	
	CU	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in $\text{Al-Al}_2\text{O}_3\text{-Ag}_2\text{-xSe}_{1+x}$ thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg_4I_5 , Solid State Ionics 70/71 (1994) 72-76.	
	CW	Boolchand, P., The maximum in glass transition temperature (T_g) near $x=1/3$ in GexSe_{1-x} Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
✓	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
✓	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in	

V. Yegorov 03/01/05

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known	
			Application Number	NEW 01736617
			Filing Date	December 18, 2003
			First Named Inventor	Kristy A. Campbell
			Art Unit	MA 2329
			Examiner Name	Not Yet Assigned - Yevsi Kov
Sheet	3	of	8	Attorney Docket Number M4065.0698/P698-A

v4		steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CA1	Boalchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CB1	Boalchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CC1	Boalchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe1-x glasses, Solid state comm. 45 (1983) 183-185.	
	CD1	Boalchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (Tg), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
	CE1	Boalchand, P.; Grothaus, J. Molecular Structure of Melt-Quenched GeSe2 and GeS2 glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.	
	CF1	Bresser, W.; Boalchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CG1	Bresser, W.J.; Boalchand, P.; Suranyi, P.; de Neufville, J.P. Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
	CH1	Bresser, W.J.; Boalchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe2 glass, Hyperfine Interactions 27 (1986) 389-392.	
	CI1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chemyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe2 Crystals, Science 258 (1992) 271-274.	
	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
	CR1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
	CU1	Orusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
v4	CV1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag2-xSe1+x/n-Si diodes, Thin Solid Films 110 (1983) 107-113.	

v. Yevsi Kov 03/01/05

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		Examiner Name	Not Yet Assigned Ye vsi Ko ✓
Sheet	4	of	8
		Attorney Docket Number	M4065.0698/P698-A

✓	CW1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous GexSe1-x photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.	
✓	CX1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.	
	CY1	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe5.5 thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.	
	CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge21Se17Te82, Indian J. Phys. 70A (1996) 507-516.	
	CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
	CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.	
	CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.	
	CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge20BixSe80-x films, Thin Solid Films 376 (2000) 238-240.	
	CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.	
	CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se75Ge7Sb18, Vacuum 43 (1992) 253-257.	
	CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.	
	CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.	
	CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe2 thin films, Phys. Rev. B 38 (1988) 12388-12403.	
	CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.	
	CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.	
	CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.	
	CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag2Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.	
	CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.	
	CO2	Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.	
	CP2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoel, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.	
✓	CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.	
✓	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	

V. Gershner

03/01/05

Substitute for form 1449A/B/PTO <h2 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center;">(Use as many sheets as necessary)</p>		Complete If Known Application Number NEW 10734617 Filing Date December 12, 2003 First Named Inventor Kristy A. Campbell Art Unit N/A 2824 Examiner Name Not Yet Assigned Yevsi Kov Attorney Docket Number M4065.0698/P698-A	
Sheet	5	of	8

✓	CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Apply. Phys. 54 (1983) 1950-1954.	
↑	CT2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.	
	CU2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.	
	CV2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.	
	CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.	
	CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
	CY2	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.	
	CZ2	Helbert et al., Intralevel hybrid resist process with submicron capability, SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CA3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V2 amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.	
	CB3	Hosokawa, S., Atomic and electronic structures of glassy GexSe1-x around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.	
	CC3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.	
	CD3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B 74 (1996) 37-50.	
	CE3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.	
	CF3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.	
	CG3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge2S3, J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.	
	CH3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.	
	CI3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.	
	CJ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As2Se7 before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.	
	CK3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As2Se5, Mat. Res. Bull. 8 (1973) 433-442.	
	CL3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.	
	CM3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1996) 9096-9104.	
N	CN3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Agx(GeSe3)1-x (0<x<=0.571) glasses, Solid state Ionics 123 (1999) 259-269.	

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		Examiner Name	Not Yet Assigned - Yevs: Kpv
		Attorney Docket Number	M4065.0698/P698-A
Sheet	6	of	8

✓	CO3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.	7
✓	CP3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.	
	CQ3	Kozicki, et al., "Applications of Programmable Resistance Changes in Metal-doped Chalcogenides", Proceedings of the 1999 Symposium on Solid State Ionic Devices, Editors - E.D. Wachsman et al., The Electrochemical Society, Inc., 1 - 12 (1999).	
	CR3	Kozicki, et al., Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures, 27, 485-488 (2000).	
	CS3	Kozicki, et al., Nanoscale phase separation in Ag-Ge-Se glasses, Microelectronic Engineering, vol. 63/1-3, 155-159 (2002).	
	CT3	M.N. Kozicki and M. Mitkova, Silver incorporation in thin films of selenium rich Ge-Se glasses, Proceedings of the XIX International Congress on Glass, Society for Glass Technology, 226-227 (2001).	
	CU3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.	
	CV3	Lakshminarayan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.	
	CW3	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.	
	CX3	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.	
	CY3	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.	
	CZ3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO2 system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.	
	CA4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.	
	CB4	Mazurier, F.; Levy, M.; Souquet, J.L. Reversible and irreversible electrical switching in TeO2-V2O5 based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.	
	CC4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 26 (1991) 253-258.	
	CD4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.	
	CE4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.	
	CF4	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.	
	CG4	Miyatani, S.-y., Electronic and ionic conduction in (AgxCu1-x)2Se, J. Phys. Soc. Japan 34 (1973) 423-432.	
	CH4	Miyatani, S.-y., Ionic conduction in beta-Ag2Te and beta-Ag2Se, Journal Phys. Soc. Japan 14 (1959) 896-1002.	
	CI4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.	
	CJ4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.	
✓	CK4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.	

V. Yegorov 03/01/05

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Substitute for form 1448A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete If Known		
			Application Number	NEW- 16736617	
			Filing Date	December 22, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	N/A 2829	
			Examiner Name	Not Yet Assigned - Yevsi Kov	
Sheet	7	of	8	Attorney Docket Number	M4065.0698/P698-A

✓	CL4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GexSe1-x amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.	
	CM4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.	
	CN4	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209.	
	CO4	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.	
	CP4	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.	
	CQ4	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54	
	CR4	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.	
	CS4	Owen, A.E.; Le Comber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.	
	CT4	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.	
	CU4	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.	
	CV4	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.	
	CW4	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.	
	CX4	Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.	
	CY4	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.	
	CZ4	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.	
	CA5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.	
	CB5	Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.	
	CC5	Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.	
	CD5	Schwocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J. Non-Cryst. Solids 29 (1978) 397-407.	
	CE5	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.	
	CF5	Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.	
	CG5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
✓	CH5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.	

V. Yevsi Kov 03/01/05

Substitute for form 1449A/B/PTO <h2 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center;">(Use as many sheets as necessary)</p>		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>NEW-101736619</td> </tr> <tr> <td>Filing Date</td> <td>December 12, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Kristy A. Campbell</td> </tr> <tr> <td>Art Unit</td> <td>N/A 2829</td> </tr> <tr> <td>Examiner Name</td> <td>Not Yet Assigned Yersikov</td> </tr> <tr> <td>Attorney Docket Number</td> <td>M4065.0698/P698-A</td> </tr> </table>		Application Number	NEW-101736619	Filing Date	December 12, 2003	First Named Inventor	Kristy A. Campbell	Art Unit	N/A 2829	Examiner Name	Not Yet Assigned Yersikov	Attorney Docket Number	M4065.0698/P698-A
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Attorney Docket Number	M4065.0698/P698-A														
Sheet	8	of	8												

14	C15	Steventon, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.	7
	CJ5	Steventon, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.	
	CK5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.	
	CL5	Tanaka, K., Ionic and mixed conductions in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.	
	CM5	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.	
	CN5	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.	
	CO5	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.	
	CP5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612.	
	CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, J. Non-Cryst. Solids 261 (2000) 277-281.	
	CR5	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.	
	CS5	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, 9-13 September 1985.	
	CT5	Tregouet, Y.; Bernede, J.C., Silver movements in Ag2Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.	
	CU5	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst. Solids 117-118 (1990) 219-221.	
	CV5	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.	
	CV6	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.	
	CV7	Vodencharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454.	
	CV8	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.	
	CV9	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.	
14	CV10	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope dTg/d<m> at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.	

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				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 2829 B
Examiner Name	R. Rocchegiani	VYEVSIK			
Attorney Docket Number	M4065.0698/P698-A				
Sheet	1	of	5		

U. S. PATENT DOCUMENTS					
Exami ner Initials	Cite No.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
VY	**AA	2002/0072188	6/13/2002	Gilton	
A	**AB	2002/0106849	08/08/2002	Moore	
	**AC	2002/0123169	09/05/2002	Moore et al.	
	**AH	2002/0123248	09/05/2002	Moore et al.	
	**AI	2002/0132417	09/09/2002	Li	
	**AJ	2002/0160551	10/31/2002	Harshfield	
	**AK	2002/0168852	11/14/2002	Harshfield et al.	
	**AL	2002/0190289	12/19/2002	Harshfield et al.	
	**AF	2003/0032254	02/13/2003	Gilton	
	**AG	2003/0038301	02/27/2003	Moore	
	**AM	2003/0043631	03/06/2003	Gilton et al.	
	**AN	2003/0045049	03/06/2003	Campbell et al.	
	**AO	2003/0045054	03/06/2003	Campbell et al.	
	**AP	2003/0047765	03/13/2003	Campbell	
	**AQ	2003/0047772	03/13/2003	Li	
	**AR	2003/0047773	03/13/2003	Li	
	**AS	2003/0048519	03/13/2003	Kozicki	
	**AT	2003/0048744	3/2003	Ovshinsky et al.	
	**AU	2003/0049912	03/13/2003	Campbell et al.	
	**AV	2003/0068861	04/10/2003	Li	
	**AW	2003/0068862	04/10/2003	Li	
	**AX	2003/0095426	05/22/2003	Hush et al.	
	**AY	2003/0096497	05/22/2003	Moore et al.	
	**AZ	2003/0107105	06/12/2003	Kozicki	
	**AA1	2003/0117831	06/26/2003	Hush	
	**AB1	2003/0128612	07/10/2003	Moore et al.	
	**AC1	2003/0137869	07/24/2003	Kozicki	
	**AD1	2003/0143782	07/31/2003	Gilton et al.	
	**AE1	2003/0155589	08/21/2003	Campbell et al.	
	**AF1	2003/0155606	08/21/2003	Campbell et al.	
	**AG1	2003/0156447	08/21/2003	Kozicki	
	**AH1	2003/0156463	08/21/2003	Casper et al.	
	**AI1	2003/0209728	11/13/2003	Kozicki et al.	
	**AJ1	2003/0209971	11/13/2003	Kozicki et al.	
	**AK1	2003/0210564	11/13/2003	Kozicki et al.	
	**AL1	2003/0212724	11/2003	Ovshinsky et al.	
	**AM1	2003/0212725	11/2003	Ovshinsky et al.	
	**AN1	2004/0035401	2/2004	Ramachandran et al.	
	**AO1	3,271,591	9/1986	Ovshinsky	
	**AP1	3,622,319	11/1971	Sharp	
	**AQ1	3,743,847	7/1973	Boland	
	**AR1	3,961,314	6/1976	Klose et al.	
VY	**AS1	3,966,317	6/1976	Wacks et al.	
VY	**AT1	3,983,542	11/1976	Ovshinsky	

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				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 9
				Examiner Name	R. Rechehiani Yevaitov
Sheet	2	of	5	Attorney Docket Number	M4065.0698/P698-A

V4	**AU1	3,988,720	10/1976	Ovshinsky	
4	**AV1	4,177,474	12/1979	Ovshinsky	
	**AW1	4,267,261	5/1981	Hallman et al.	
	**AX1	4,269,935	5/1981	Masters et al.	
	**AY1	4,312,938	1/1982	Drexler, et al.	
	**AZ1	4,320,191	3/1982	Yoshikawa et al.	
	**AA2	4,405,710	9/1983	Balasubramanyam et al.	
	**AB2	4,499,557	2/1985	Holmberg et al.	
	**AC2	4,597,162	7/1986	Johnson et al.	
	**AD2	4,608,296	8/1986	Keem et al.	
	**AE2	4,637,885	1/1987	Ovshinsky et al.	
	**AF2	4,646,266	2/1987	Ovshinsky et al.	
	**AG2	4,664,939	5/1987	Ovshinsky	
	**AH2	4,668,968	5/1987	Ovshinsky et al.	
	**AI2	4,670,763	6/1987	Ovshinsky et al.	
	**AJ2	4,673,957	6/1987	Ovshinsky et al.	
	**AK2	4,678,679	7/1987	Ovshinsky	
	**AL2	4,696,758	9/1987	Ovshinsky et al.	
	**AM2	4,698,234	10/1987	Ovshinsky et al.	
	**AN2	4,710,899	12/1987	Young et al.	
	**AO2	4,728,406	3/1988	Banerjee et al.	
	**AP2	4,737,379	4/1988	Hudgens et al.	
	**AQ2	4,766,471	8/1988	Ovshinsky et al.	
	**AR2	4,769,338	9/1988	Ovshinsky et al.	
	**AS2	4,775,425	10/1988	Guha et al.	
	**AT2	4,788,594	11/1988	Ovshinsky et al.	
	**AU2	4,795,657	1/1989	Formigoni et al.	
	**AV2	4,809,044	2/1989	Pryor et al.	
	**AW2	4,818,717	4/1989	Johnson et al.	
	**AX2	4,843,443	6/1989	Ovshinsky et al.	
	**AY2	4,845,533	7/1989	Pryor et al.	
	**AZ2	4,847,674	7/1989	Sliwa et al.	
	**AA3	4,853,785	8/1989	Ovshinsky et al.	
	**AB3	4,891,330	1/1990	Guha et al.	
	**AC3	5,128,099	7/1992	Strand et al.	
	**AD3	5,159,661	10/1992	Ovshinsky et al.	
	**AE3	5,166,758	11/1992	Ovshinsky et al.	
	**AF3	5,177,567	1/1993	Klarsy et al.	
	**AG3	5,219,788	6/1993	Abermathey et al.	
	**AH3	5,238,862	8/1993	Bialock et al.	
	**AI3	5,296,716	3/1994	Ovshinsky et al.	
	**AJ3	5,315,131	5/1994	Kishimoto et al.	
	**AK3	5,335,219	8/1994	Ovshinsky et al.	
	**AL3	5,341,328	8/1994	Ovshinsky et al.	
	**AM3	5,350,484	9/1994	Gardner et al.	
	**AN3	5,359,205	10/1994	Ovshinsky	
	**AO3	5,360,981	11/1994	Owen et al.	
V4	**AP3	5,406,509	4/1995	Ovshinsky et al.	
4	**AQ3	5,414,271	5/1995	Ovshinsky et al.	

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				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 9
				Examiner Name	R. Reechegant-Yersikov
Sheet	3	of	5	Attorney Docket Number	M4065.0698/P698-A

✓	**AR3	5,512,328	4/1996	Yoshimura et al.	
✓	**AS3	5,512,773	4/1996	Wolf et al.	
	**AT3	5,534,711	7/1996	Ovshinsky et al.	
	**AU3	5,534,712	7/1996	Ovshinsky et al.	
	**AV3	5,538,947	7/1996	Klersy et al.	
	**AW3	5,543,737	8/1996	Ovshinsky	
	**AX3	5,591,501	1/1997	Ovshinsky et al.	
	**AY3	5,596,522	1/1997	Ovshinsky et al.	
	**AZ3	5,687,112	11/1997	Ovshinsky	
	**AA4	5,694,054	12/1997	Ovshinsky et al.	
	**AB4	5,714,768	2/1998	Ovshinsky et al.	
	**AC4	5,726,083	3/1998	Takaishi	
	**AD4	5,789,277	8/1998	Zahorik et al.	
	**AE4	5,814,527	9/29/1998	Wolstenholme et al	
	**AF4	5,818,749	10/06/1998	Harshfield	
	**AG4	5,825,046	10/1998	Czubatyj et al.	
	**AH4	5,841,150	11/1998	Gonzalez et al.	
	**AI4	5,846,889	12/1998	Harbison et al.	
	**AJ4	5,851,882	12/22/1998	Harshfield	
	**AK4	5,869,843	2/9/1999	Harshfield	
	**AL4	5,896,312	4/20/1999	Kozicki et al.	
	**AM4	5,912,839	6/1999	Ovshinsky et al.	
	**AN4	5,914,893	6/22/1999	Kozicki et al.	
	**AO4	5,933,365	8/1999	Klersy et al.	
	**AP4	5,998,066	12/1999	Block et al.	
	**AQ4	6,011,757	1/2000	Ovshinsky	
	**AR4	6,031,287	2/29/2000	Harshfield	
	**AS4	6,077,729	6/2000	Harshfield	
	**AT4	6,084,796	7/4/2000	Kozicki et al.	
	**AU4	6,087,674	7/2000	Ovshinsky et al.	
	**AV4	6,141,241	10/2000	Ovshinsky et al.	
	**AW4	6,177,338	1/2001	Llaw et al.	
	**AX4	6,117,720	9/2000	Harshfield	
	**AY4	6,143,604	11/2000	Chiang et al.	
	**AZ4	6,236,059	5/2001	Wolsteinholme et al.	
	**AA5	6,274,805	08/2001	Nakazawa et al.	
	**AB5	6,297,170	10/2001	Gabriel et al.	
	**AC5	6,300,684	10/2001	Gonzalez et al.	
	**AD5	6,316,784	11/2001	Zahorik et al.	
	**AE5	6,329,606	12/2001	Freyman et al.	
	**AF5	6,339,544	1/2002	Chiang et al.	
	**AG5	6,348,365	2/19/2002	Moore et al.	
	**AH5	6,350,879	2/2002	McDaniel et al.	
	**AI5	6,376,284	4/2002	Gonzalez et al.	
	**AJ5	6,391,688	5/2002	Gonzalez et al.	
	**AK5	6,404,665	6/2002	Lowery et al.	
	**AL5	6,414,376	7/2002	Thakur et al.	
✓	**AM5	6,418,049	7/9/2002	Kozicki et al.	
✓	**AN5	6,420,725	7/16/2002	Harshfield	

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				Examiner Name	R. Rocchegiani Yevsikov
				Attorney Docket Number	M4065.0698/P698-A
Sheet	4	of	5		

V4	**AO5	6,423,628	7/2002	Li et al.	
	**AP5	6,429,064	8/2002	Wicker	
	**AQ5	6,437,383	8/2002	Xu	
	**AR5	6,440,837	8/27/2002	Harshfield	
	**AS5	6,462,984	10/2002	Xu et al.	
	**AT5	6,480,438	11/2002	Park	
	**AU5	6,487,113	11/2002	Park et al.	
	**AV5	6,501,111	12/2002	Lowery	
	**AW5	6,507,061	1/2003	Hudgens et al.	
	**AX5	6,511,862	1/2003	Hudgens et al.	
	**AY5	6,511,867	1/2003	Lowery et al.	
	**AZ5	6,512,241	1/2003	Lai	
	**AA6	6,514,805	2/2003	Xu et al.	
	**AB6	6,531,373	3/2003	Gill et al.	
	**AC6	6,534,781	3/2003	Dennison	
	**AD6	6,545,287	4/2003	Chiang	
	**AE6	6,545,907	4/2003	Lowery et al.	
	**AF6	6,555,860	4/2003	Lowery et al.	
	**AG6	6,563,164	5/2003	Lowery et al.	
	**AH6	6,566,700	5/2003	Xu	
	**AI6	6,567,293	5/2003	Lowery et al.	
	**AJ6	6,569,705	5/2003	Chiang et al.	
	**AK6	6,570,784	5/2003	Lowery	
	**AL6	6,576,921	6/2003	Lowery	
	**AM6	6,586,761	7/2003	Lowery	
	**AN6	6,589,714	7/2003	Maimon et al.	
	**AO6	6,590,807	7/2003	Lowery	
	**AP6	6,593,176	7/2003	Dennison	
	**AQ6	6,597,009	7/2003	Wicker	
	**AR6	6,605,527	8/2003	Dennison et al.	
	**AS6	6,613,604	9/2003	Maimon et al.	
	**AT6	6,621,095	9/2003	Chiang et al.	
	**AU6	6,625,054	9/2003	Lowery et al.	
	**AV6	6,638,820	10/2003	Moore	
	**AW6	6,642,102	11/2003	Xu	
	**AX6	6,646,297	11/2003	Dennison	
	**AY6	6,649,928	11/2003	Dennison	
	**AZ6	6,667,900	12/2003	Lowery et al.	
	**AA7	6,671,710	12/2003	Ovshinsky et al.	
	**AB7	6,673,648	1/2004	Lowrey	
	**AC7	6,673,700	1/2004	Dennison et al.	
	**AD7	6,674,115	1/2004	Hudgens et al.	
	**AE7	6,687,427	2/2004	Ramalingam et al.	
	**AF7	6,690,026	2/2004	Peterson	
	**AG7	6,696,355	2/2004	Dennison	
	**AH7	6,687,153	2/2004	Lowery	
V4	**AI7	6,707,712	3/2004	Lowery	
V4	**AJ7	6,714,954	3/2004	Ovshinsky et al.	

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2828 9
				Examiner Name	R. Rocchegiani Yevsi KOV
Sheet	5	of	5	Attorney Docket Number	M4065.0698/P698-A

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.†	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*
		Country Code‡	Number* Kind Code§ (if known)				
✓	**BA	JP	5-6126916	10/19981	Akira et al.		
✓	**BB	WO	00/48196	08/17/2000	Kozicki et al.		
✓	**BC	WO	02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	V. Yevsi KOV	Date Considered	03/01/05
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